



TAYCHIPST SILICON RECTIFIER DIODES

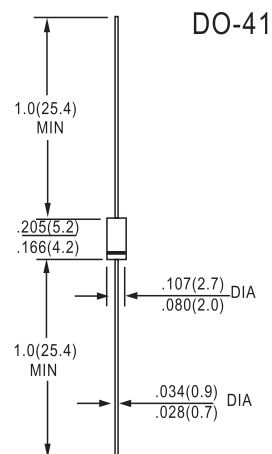
S5566B THRU S5566N**100V-1000V 1.0A**

FEATURES

- * High current capability
- * High surge current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * Pb / RoHS Free

Mechanical Data

- * Case : DO-41 Molded plastic
- * Epoxy : UL94V-O rate flame retardant
- * Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
- * Polarity : Color band denotes cathode end
- * Mounting position : Any
- * Weight : 0.339 gram



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 50 Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

RATING	SYMBOL	S5566B	S5566G	S5566J	S5566N	UNIT
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	100	400	600	1000	V
Maximum RMS voltage	V_{RMS}	70	280	420	700	V
Maximum DC Blocking Voltage	V_{DC}	100	400	600	1000	V
Maximum Average Forward Current	$I_{F(AV)}$	1.0				A
Maximum Peak Forward Surge Current Single half sine wave superimposed on rated load (JEDEC Method)	I_{FSM}	(50Hz) 45	(60Hz) 49	(50Hz) 30	(60Hz) 33	A
Maximum Forward Voltage at $I_F = 1.0$ A	V_F	1.2				V
Maximum Repetitive Peak Reverse Current	I_{RRM}	10				μA
Junction Temperature Range	T_J	- 40 to + 150				°C
Storage Temperature Range	T_{STG}	- 40 to + 150				°C



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FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

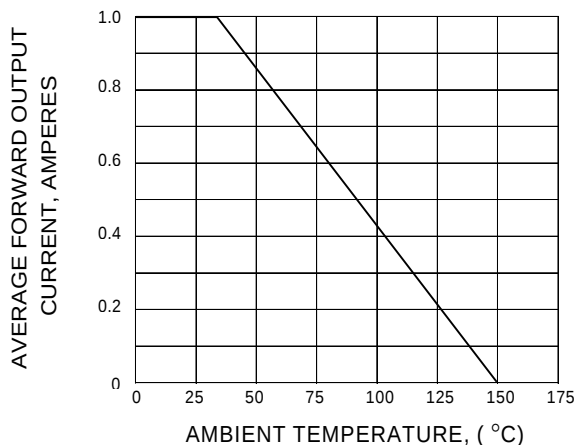


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

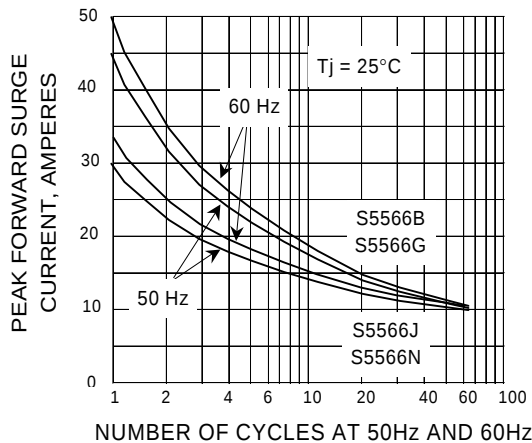


FIG.3 - TYPICAL FORWARD CHARACTERISTICS

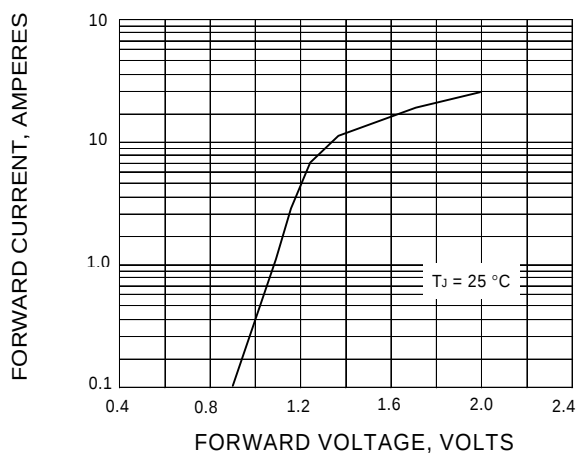


FIG.4 - TYPICAL REVERSE CHARACTERISTICS

